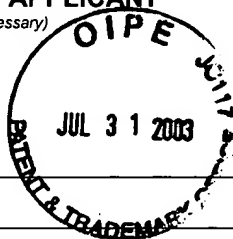


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Application Number	09/691004
Filing Date	October 18, 2000
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Mondt, Johannes

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Attorney Docket No: 303.324US4

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-3,792,465	02/12/1974	Collins, D. R., et al.	340	324 R	12/30/1971
	US-4,118,795	10/03/1978	Frye, R. C., et al.	365	222	08/27/1976
	US-4,384,349	05/17/1983	McElroy, D J.	365	185.02	06/02/1980
	US-4,816,883	03/28/1989	Baldi, Livio	357	23.5	06/22/1987
	US-4,897,710	01/30/1990	Suzuki, A., et al.	357	71	08/18/1997
	US-5,317,535	05/31/1994	Talreja, Sanjay S., et al.	365	185	06/19/1992
	US-5,366,713	11/22/1994	Sichanugrist, P., et al.	423	346	05/28/1993
	US-5,388,069	02/07/1995	Kokubo, Masaya	365	185	03/18/1993
	US-5,424,993	06/13/1995	Lee, Roger R., et al.	365	218	11/15/1993
	US-5,438,544	08/01/1995	Makino, Takami	365	185	01/28/1994
	US-5,441,901	08/15/1995	Candelaria, J.	437	31	06/10/1994
	US-5,467,306	11/14/1995	Kaya, Cetin, et al.	365	185.2	10/04/1993
	US-5,493,140	02/20/1996	Iguchi, Katsuji	257	316	06/21/1994
	US-5,672,889	09/30/1997	Brown,	257	77	
	US-5,828,101	10/27/1998	Endo, K.	257	330	03/25/1996
	US-5,861,346	01/19/1999	Hamza, A. et al.	438	869	07/27/1995
	US-5,912,837	06/15/1999	Lakhani,	365	185.02	10/28/1996
	US-5,926,740	07/20/1999	Forbes, L., et al.	438	763	10/27/1997
	US-6,297,521	10/02/2001	Forbes, L., et al.	257	76	08/14/1998
	US-6,307,775	10/23/2001	Forbes, L., et al.	365	185.01	08/27/1998
	US-6,309,907	10/30/2001	Forbes, L., et al.	438	108	08/21/1998

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		BELTRAM, F., et al., "GaAlAs/GaAs Floating-Gate Memory Devices with Graded-Gap Injector Grown by Molecular-Beam Epitaxy", <u>IEEE Transactions on Electron Devices</u> , 35, Abstract No. VA-7, (Dec. 1988), pp. 2451	
		BELTRAM, F., et al., "Memory phenomena in heterojunction structures: Evidence for suppressed thermionic emission", <u>Appl. Phys. Lett.</u> , 53(5), (1988), pp. 376-378	
		BOERINGER, DANIEL W., et al., "Avalanche amplification of multiple resonant tunneling through parallel silicon microcrystallites", <u>Physical Rev. B</u> , 51, (1995), pp. 13337-13343	

EXAMINER

J. MONDT

DATE CONSIDERED

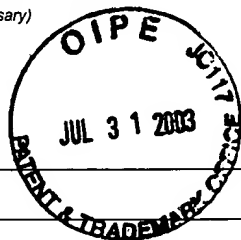
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Application Number	09/691004
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		BURNS, S. G., et al., In: <u>Principles of Electronic Circuits</u> , West Publishing Co., St. Paul, MN, (1987), pp. 382-383	
		BURNS, S., et al., In: <u>Principles of Electronic Circuits</u> , West Publishing Company, (1987), pg. 380	
		CAPASSO, F., et al., "New Floating-Gate AlGaAs/GaAs Memory Devices with Graded-Gap Electron Injector and Long Retention Times", <u>IEEE Electron Device Letters</u> , (1988), pp. 377-379	
		EDELBERG, E., et al., "Visible Luminescence from Nanocrystalline silicon films produced by plasma enhanced chemical vapor deposition", <u>Appl. Phys. Lett.</u> , 68 , (1996), pp. 1415-1417	
		HYBERTSEN, MARK S., "Absorption and Emission of Light in Nanoscale Silicon Structures", <u>Phys. Rev. Lett.</u> , 72 , (1994), pp. 1514-1517	
		KATO, MASATAKA, et al., "Read-Disturb Degradation Mechanism due to Electron Trapping in the Tunnel Oxide for Low-voltage Flash Memories", <u>IEEE Electron Device Meeting</u> , (1994), pp. 45-48	
		LOTT, J., et al., "Anisotropic thermionic emission of electrons contained in GaAs/AlAs floating gate device structures", <u>Appl. Phys. Lett.</u> , 55 (12), (1989), pp. 1226-1228	
		LOTT, J. A., et al., "Charge Storage in InAlAs/InGaAs/InP Floating Gate Heterostructures", <u>Electronics Letters</u> , 26 , (July 5, 1990), pp. 972-973	
		MOHAMMAD, S. N., et al., "Emerging Gallium Nitride Based Devices", <u>Proceedings of the IEEE</u> , 83 , (Oct. 1995), pp. 1306-1355	
		NEUDECK, P., et al., "Electrical Characterization of a JFET-Accessed GaAs Dynamic RAM Cell", <u>IEEE Electron Device Letters</u> , 10 (11), (1989), pp. 477-480	
		NG, K., In: <u>Complete Guide To Semiconductor Devices</u> , McGraw-Hill, Inc. New York, (1995), pp. 322-328, 605-608	
		QIAN, Q., et al., "Multi-Day Dynamic Storage of Holes at the AlAs/GaAs Interface", <u>IEEE Electron Device Letters</u> , EDL-7 (11), (1986), pp. 607-609	
		RUSKA, W. S., "Microelectronic Processing", <u>McGraw-Hill Book Co.</u> , (1987), pp. 281	
		SCHOENFELD, O., et al., "Formation of Si Quantum dots in Nanocrystalline silicon", <u>Proc. 7th Int. Conf. on Modulated Semiconductor Structures, Madrid</u> , (1995), pp. 605-608	
		SHARMA, B., et al., "Heterojunction Devices", In: <u>Semiconductor Heterojunctions</u> , Pergamon Press, New York, (1974), pp. 133-137	
		STREETMAN, B., In: <u>Solid State Electronic Devices</u> , 4th Edition, Prentice Hall, New Jersey, (1995), pp. 217-219, 392-394	
		SZE, S. M., In: <u>Physics of Semiconductor Devices</u> , 2nd Edition, John Wiley & Sons, New York, (1981), pp. 122-129, 700-703, 708-710, 763-765	
		TSU, RAPHAEL, et al., "Slow Conductance oscillations in nanoscale silicon clusters of quantum dots", <u>Appl. Phys. Lett.</u> , 65 , (1994), pp. 842-844	

EXAMINER

J. MONDT

DATE CONSIDERED

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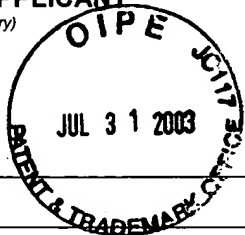
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		WOLF, S., "Semiconductor Memory Process Integration", <u>Silicon Processing for The VLSI Era, Volume 2: Process Integration</u> , (1990), pp. 623-628	
		YE, QIU-YI, et al., "Resonant Tunneling via Microcrystalline-silicon quantum confinement", <u>Physical Rev. B</u> , 44, (1991), pp. 1806-1811	
		ZHAO, X., et al., "Nanocrystalline Si: a material constructed by Si quantum dots", <u>1st Int. Conf. on Low Dimensional Structures and Devices, Singapore</u> , (1995), pp. 467-471	

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